

ABSTRACT OF THE DISCLOSURE

A semiconductor device has a MOSFET. The MOSFET includes source and drain regions, a gate insulating film, a gate electrode, and first, second, and third metal silicide films. The source and drain regions are formed in the major surface region of a semiconductor substrate. The gate insulating film is formed on the channel region between the source and drain regions. The gate electrode is formed on the gate insulating film and includes a poly- $\text{Si}_{1-x}\text{Ge}_x$ layer having a $\text{Ge}/(\text{Si}+\text{Ge})$ composition ratio \underline{x} ($0 < x < 0.2$). The first metal silicide film is formed on the gate electrode and made of $\text{NiSi}_{1-y}\text{Ge}_y$. The second and third metal silicide films are formed on the source and drain regions, respectively, and made of NiSi .